

電力

國立成功大學 17 學年度研究所招生考試(電子學 試題) 共 / 1
第 / 1

- (1) Explain why a contact difference of potential must develop across an open-circuited p-n junction.
 (2) Discuss the two possible sources of breakdown in a transistor as the collector-to-emitter voltage is increased.
 (3) What is a Schottky transistor? Why is storage time eliminated in such a transistor?
 (4) Explain the function of a tristate (3-state) TTL gate. (16%)
- (1) Show the truth table for the half adder, and the implementation for the digit D and the carry C.
 (2) Give the truth tables for each FLIP-FLOP type: (a) S-R; (b) J-K; (c) D; and (d) T.
 (3) What do the acronyms FAMOS mean? How is such a cell programmed? How is the cell erased?
 (4) Define f_p and f_T . What is the relationship between f_p and f_T ? (16%)
- (1) Sketch the circuit of a logarithmic amplifier using one OP AMP and explain its operation.
 (2) Show that the maximum conversion efficiency of the idealized class B push-pull power amplifier is 78.5%.
 (3) Give the Barkhausen conditions required in order for sinusoidal oscillations to be sustained.
 (4) Show the model of an OP AMP taking into account I_{B1} , I_{B2} , V_{IO} , R_i , R_o , and A_v . What is the output offset voltage in terms of parameters of this model? (16%)
- (1) Sketch the block diagram for the 5-stage twisted-ring counter.
 (2) Write the truth table of FLIP-FLOP outputs Q_4 , Q_3 , Q_2 , Q_1 , and Q_0 after each pulse. Assume that initially $Q_4 = Q_3 = Q_2 = Q_1 = Q_0 = 0$.
 (3) By what number N does this system divide.
 (4) Show that two-input AND gates can be used for decoding. (16%)
- In the circuit of Fig. 1, $R_d = r_d = 15 k\Omega$, $R_s = 2 k\Omega$, and $\mu = 24$. Find the voltage gains A_1 and A_2 defined by $V_{O2} = A_1 V_1 + A_2 V_2$. (18%)
- For the amplifier of Fig. 2, $h_{fe} = 100$, $h_{ie} = 1 k\Omega$, $R_c = 3 k\Omega$, $C_b = C_z = 100 \mu F$, $W C_z R_e \gg 1$, and the shunting effect of $R_1 \| R_2$ is negligible. It is desired that the absolute value of the midband voltage gain A_0 be more than 160, and that the lower 3-dB frequency f_L be at most 90 Hz. Find the range of values for R_s which satisfies these two requirements. (18%)

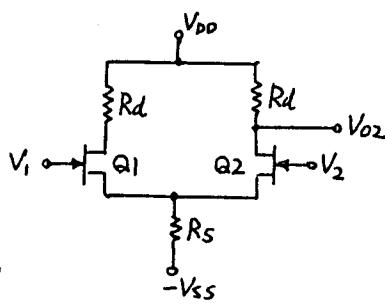


Fig. 1

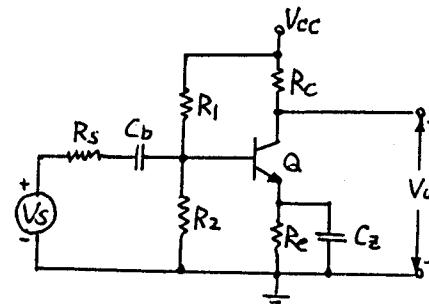


Fig. 2